



# 2SJ660 — P-Channel Silicon MOSFET

## General-Purpose Switching Device Applications

### Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 4V drive.
- Motor drive, DC / DC converter.
- Avalanche resistance guarantee.

### Specifications

#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		-60	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±20	V
Drain Current (DC)	I <sub>D</sub>		-26	A
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	-104	A
Allowable Power Dissipation	P <sub>D</sub>		1.65	W
		T <sub>c</sub> =25°C	50	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C
Avalanche Energy (Single Pulse) *1	E <sub>AS</sub>		115	mJ
Avalanche Current *2	I <sub>AV</sub>		-26	A

Note : \*1 V<sub>DD</sub>=30V, L=200μH, I<sub>AV</sub>=-26A

\*2 L≤200μH, Single pulse

#### Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> =-1mA, V <sub>GS</sub> =0V	-60			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-60V, V <sub>GS</sub> =0V			-1	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-1mA	-1.2		-2.6	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-13A	11	19		S
Static Drain-to-Source On-State Resistance	R <sub>DS(on)1</sub>	I <sub>D</sub> =-13A, V <sub>GS</sub> =-10V		46	60	mΩ
	R <sub>DS(on)2</sub>	I <sub>D</sub> =-13A, V <sub>GS</sub> =-4V		67	94	mΩ

Marking : J660

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# 2SJ660

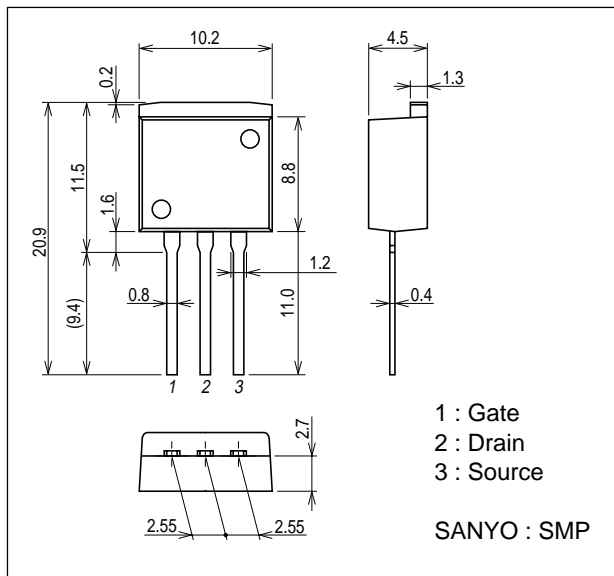
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	V <sub>DS</sub> =-20V, f=1MHz		2200		pF
Output Capacitance	Coss	V <sub>DS</sub> =-20V, f=1MHz		220		pF
Reverse Transfer Capacitance	Crss	V <sub>DS</sub> =-20V, f=1MHz		165		pF
Turn-ON Delay Time	t <sub>d(on)</sub>	See specified Test Circuit.		18		ns
Rise Time	t <sub>r</sub>	See specified Test Circuit.		150		ns
Turn-OFF Delay Time	t <sub>d(off)</sub>	See specified Test Circuit.		180		ns
Fall Time	t <sub>f</sub>	See specified Test Circuit.		130		ns
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-30V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-26A		45		nC
Gate-to-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =-30V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-26A		7.4		nC
Gate-to-Drain "Miller" Charge	Q <sub>gd</sub>	V <sub>DS</sub> =-30V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-26A		9		nC
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-26A, V <sub>GS</sub> =0V		-0.98	-1.2	V

## Package Dimensions

unit : mm

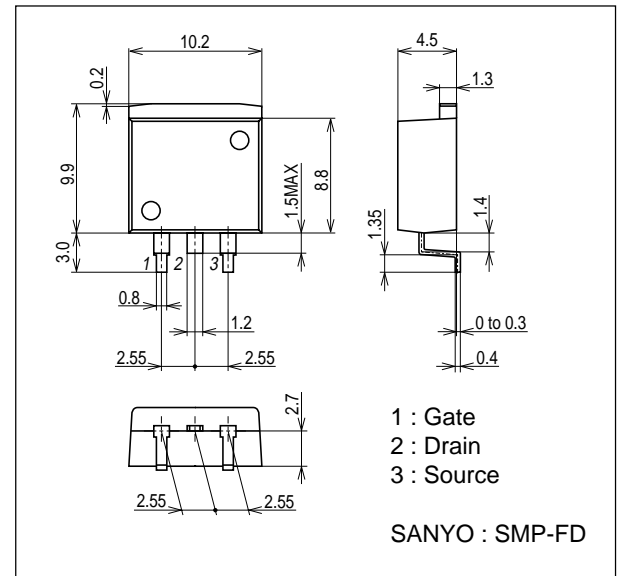
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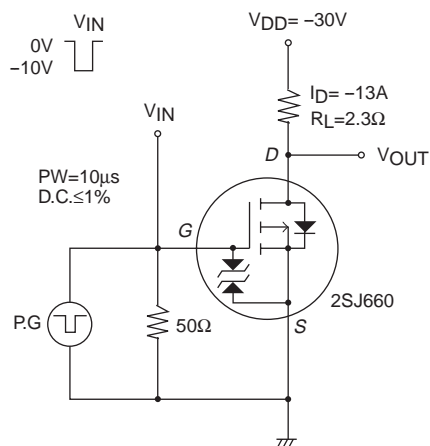
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unit : mm

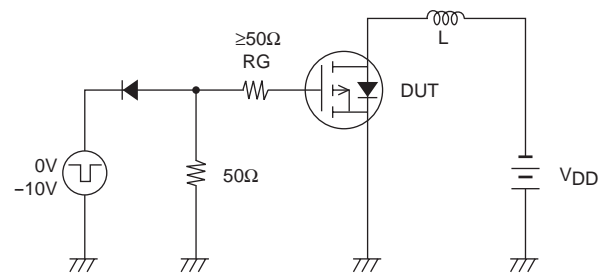
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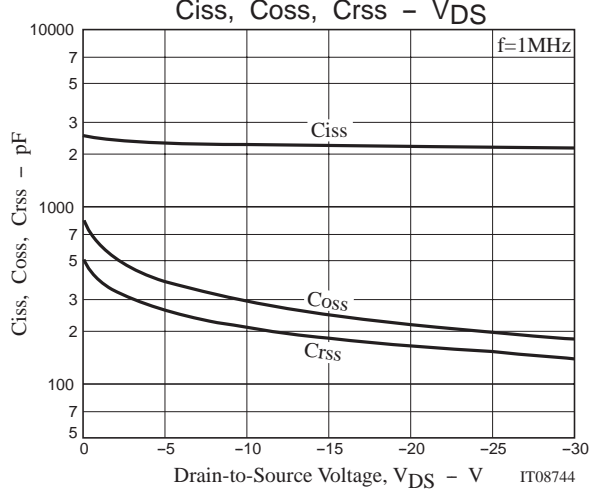
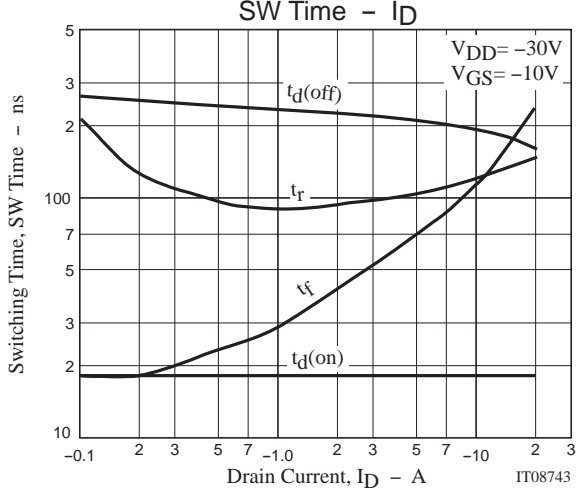
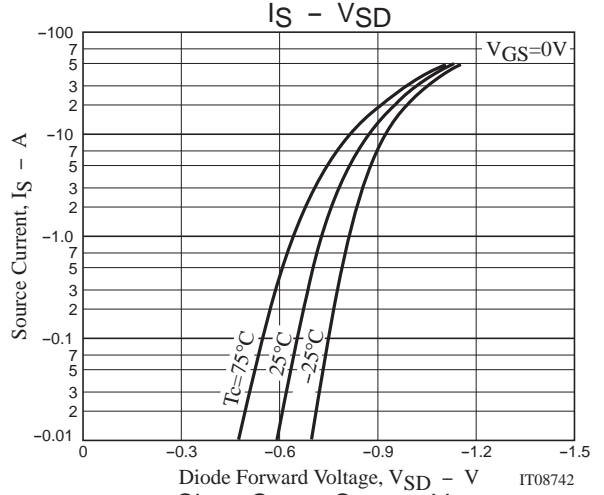
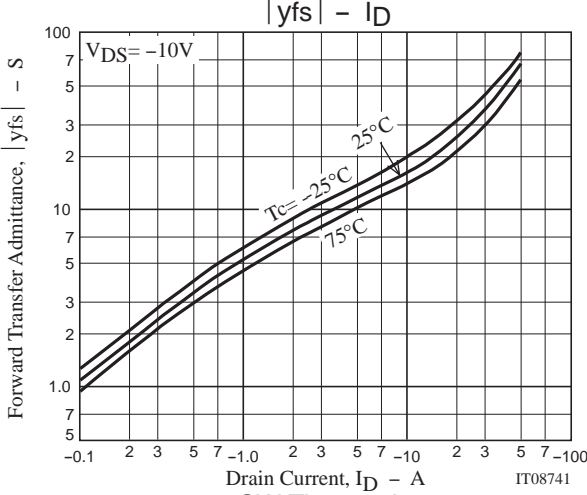
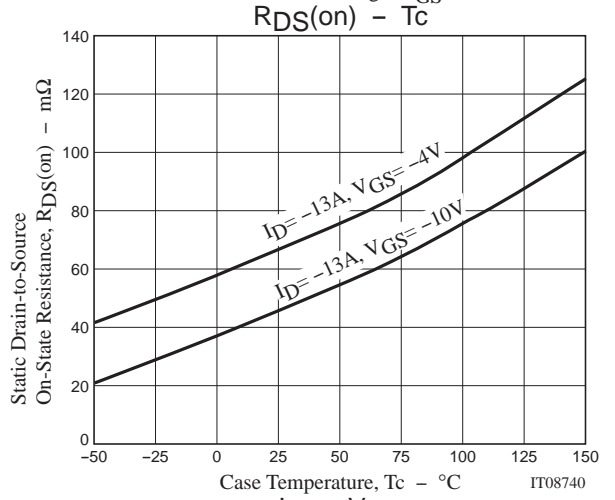
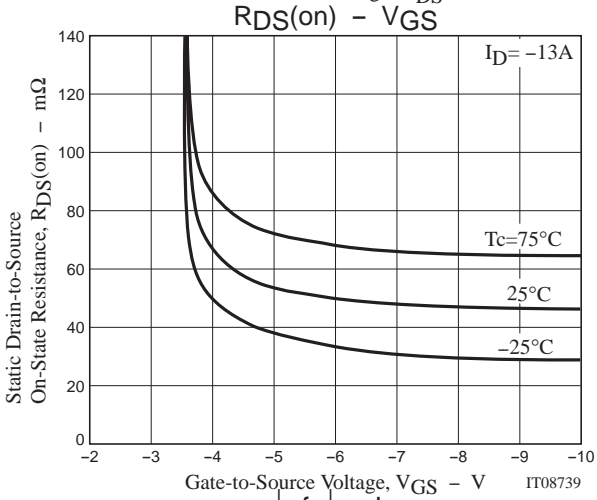
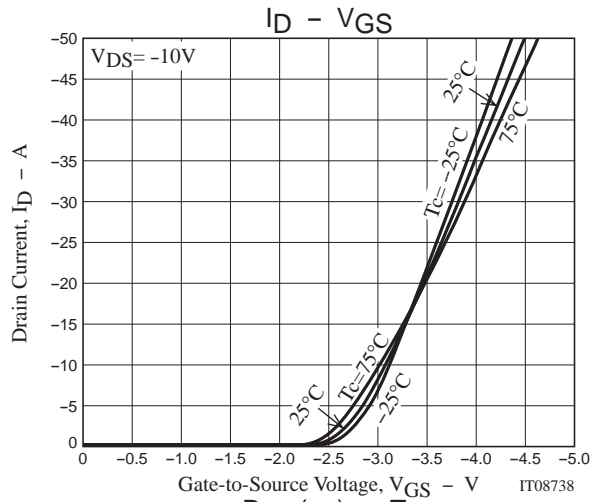
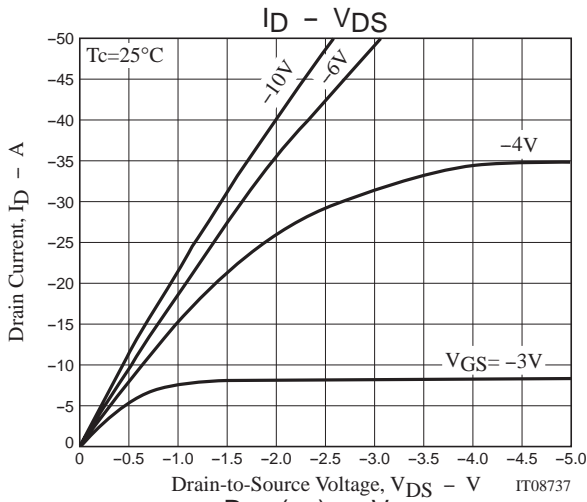
## Switching Time Test Circuit

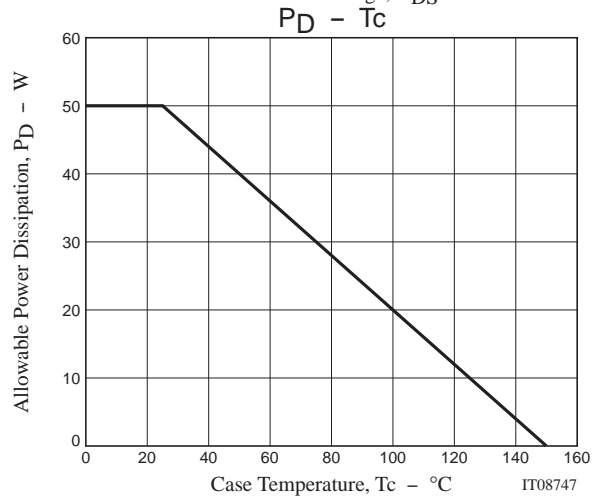
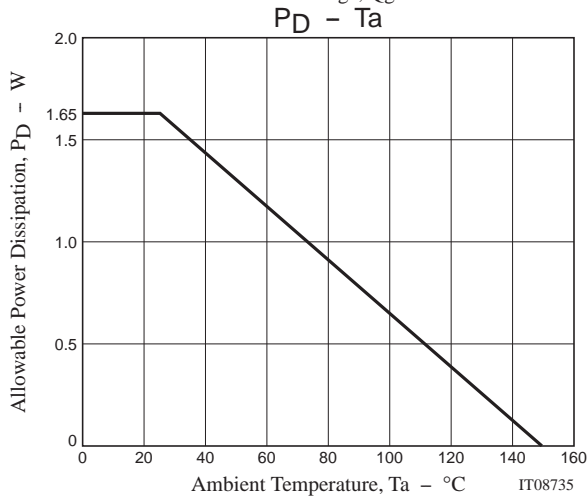
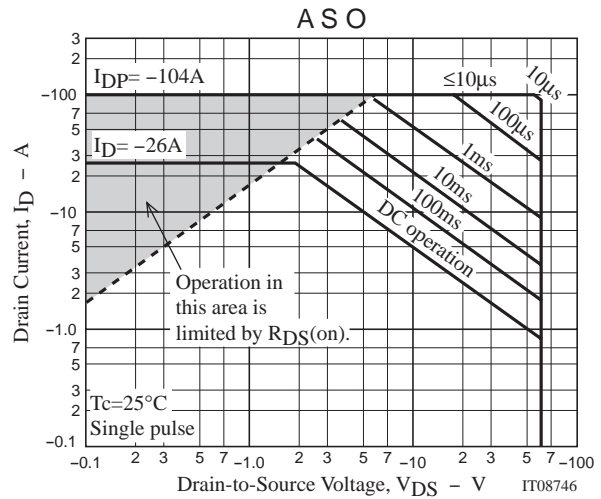
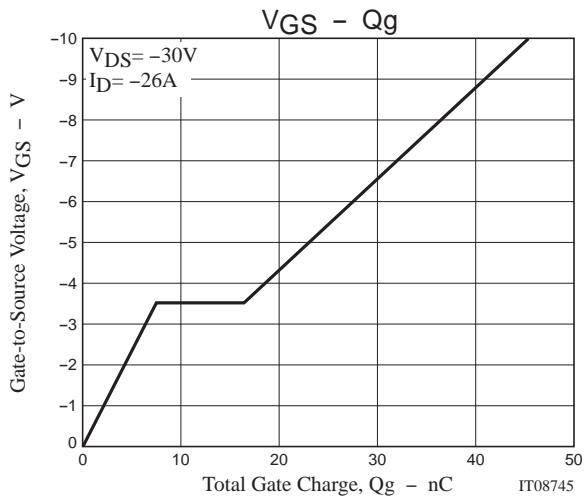


## Avalanche Resistance Test Circuit



# 2SJ660





Note on usage : Since the 2SJ660 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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